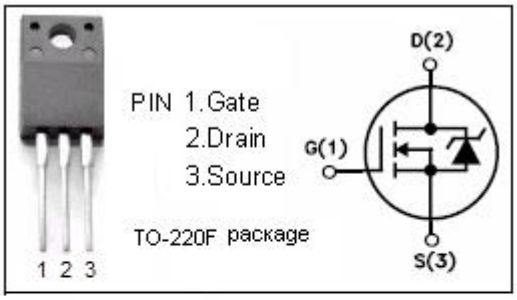
isc N-Channel MOSFET Transistor 2SK1766



DESCRIPTION

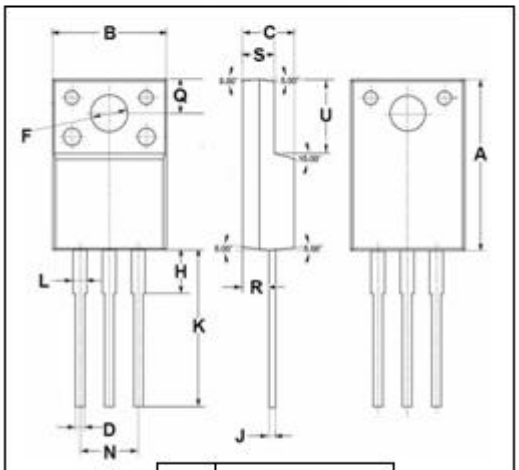
- Drain Current I_D= 10A@ T_C=25℃
- Drain Source Voltage
  : V_{DSS}= 250V(Min)
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power supplies, converters and power motor controls

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	250	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-continuous@ TC=25℃	10	A
P_{tot}	Total Dissipation@TC=25℃	40	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 1mA	250		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D=1mA	1.5	3.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 5A		0.6	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±30V;V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 250V; V_{GS}= 0		1	mA